1) Purpose: Understanding the common-emitter amplifier.

In the circuit below, assume the npn BJT is operating in forward-active mode. Let $\beta=$ $130, \mathrm{~V}_{\mathrm{A}}=60 \mathrm{~V}$, and $\mathrm{V}_{\mathrm{BE}}=0.7 \mathrm{~V}$. Assume the capacitors have negligible impedance at the frequency of the ac signal.
a. What are the purposes of capacitors $\mathrm{C}_{1}, \mathrm{C}_{2}$, and $\mathrm{C}_{3}$ in this circuit?

Capacitors $\mathrm{C}_{1}$ and $\mathrm{C}_{3}$ are coupling capacitors. Their purpose is to allow ac signals to enter/exit the circuit at particular nodes while leaving DC signals unchanged. Capacitor $\mathbf{C}_{2}$ is a bypass capacitor. Its purpose is to rout ac signals around the emitter resistor, effectively allowing the emitter to act as an ac ground.
b. Determine all DC terminal voltages and currents as well as the small-signal voltage gain $A_{v}$ of the amplifier circuit if $R_{E}=12 \mathrm{k} \Omega$.

Step 1: Obtain the DC equivalent circuit by treating capacitors as open circuits and Thevenizing the base input.


Figure 1S: The DC equivalent circuit.
Step 2: Use KVL and the assumption that the transistor is biased in forwardactive mode to determine the $\mathbf{Q}$-point currents and voltages.

Relevant transistor equations:

$$
\begin{gathered}
I_{\mathrm{C}}=\beta I_{\mathrm{B}} \\
I_{\mathrm{E}}=(\beta+\mathbf{1}) I_{\mathrm{B}}
\end{gathered}
$$

Following the left side of the circuit:

$$
V_{\mathrm{EQ}}-\left(R_{2} \| R_{4}\right) I_{\mathrm{B}}-V_{\mathrm{BE}}-R_{\mathrm{E}} I_{\mathrm{E}}=0
$$

$$
\begin{gathered}
V_{\mathrm{EQ}}-\left(R_{2} \| R_{4}\right) I_{\mathrm{B}}-V_{\mathrm{BE}}-R_{\mathrm{E}}(\beta+1) I_{\mathrm{B}}=0 \\
I_{\mathrm{B}}=\frac{V_{\mathrm{EQ}}-V_{\mathrm{BE}}}{\left(R_{2}| | R_{4}\right)+R_{\mathrm{E}}(\beta+1)} \\
=\frac{4.8 \mathrm{~V}-0.7 \mathrm{~V}}{\mathbf{9 6 k \Omega} \mathbf{~ k}+(12 \mathrm{k} \Omega) 131} \\
I_{\mathrm{B}}=2.46 \mu \mathrm{~A} \\
I_{\mathrm{C}}=\beta I_{\mathrm{B}}=130(2.46 \mu \mathrm{~A})=0.320 \mathrm{~mA} \\
I_{\mathrm{E}}=(\beta+1) I_{\mathrm{B}}=131(2.46 \mu \mathrm{~A})=0.322 \mathrm{~mA}
\end{gathered}
$$

Knowing the DC terminal currents, we can find the DC terminal voltages by again using KVL.

$$
\begin{gathered}
V_{\mathrm{B}}=V_{\mathrm{EQ}}-\left(R_{2} \| R_{4}\right) I_{\mathrm{B}}=4.8 \mathrm{~V}-(96 \mathrm{k} \Omega)(2.46 \mu \mathrm{~A}) \\
V_{\mathrm{B}}=4.56 \mathrm{~V} \\
V_{\mathrm{C}}=V_{\mathrm{CC}}-R_{\mathrm{C}} I_{\mathrm{C}}=12 \mathrm{~V}-(15 \mathrm{k} \Omega)(0.320 \mathrm{~mA}) \\
V_{\mathrm{C}}=7.20 \mathrm{~V} \\
V_{\mathrm{E}}=V_{\mathrm{B}}-V_{\mathrm{BE}}=4.56 \mathrm{~V}-0.7 \mathrm{~V} \\
V_{\mathrm{E}}=3.86 \mathrm{~V}
\end{gathered}
$$

Step 3: Obtain the ac equivalent circuit by treating all capacitors as short circuits and all DC sources as short circuits.


Figure 2S: The ac equivalent circuit.

Step 4: Obtain the Hybrid-Pi circuit by replacing the transistor with the HybridPi model. From analyzing this circuit, obtain the small-signal voltage gain.


Figure 3S: The Hybrid-Pi equivalent circuit.
The small-signal parameters, as determined from the Q-point found in Step 2, are as follows.

$$
\begin{gathered}
g_{\mathrm{m}}=\frac{I_{\mathrm{C}}}{V_{\mathrm{T}}}=\frac{0.320 \mathrm{~mA}}{0.0259 \mathrm{~V}}=12.4 \mathrm{mS} \\
r_{\pi}=\frac{\beta}{g_{\mathrm{m}}}=\frac{130}{12.4 \mathrm{mS}}=10.5 \mathrm{k} \Omega \\
r_{\mathrm{o}}=\frac{V_{\mathrm{A}}+V_{\mathrm{CE}}}{I_{\mathrm{C}}}=\frac{60 \mathrm{~V}+7.20 \mathrm{~V}-3.86 \mathrm{~V}}{0.320 \mathrm{~mA}}=198 \mathrm{k} \Omega
\end{gathered}
$$

To determine $A_{v}=v_{o u t} / v_{i n}$, we first relate $v_{i n}$ to $v_{b e}$ and then relate $v_{b e}$ to $v_{o u t}$.

$$
\begin{gathered}
v_{\mathrm{be}}=\frac{R_{2}| | R_{4}| | r_{\pi}}{R_{\mathrm{I}}+R_{2}| | R_{4}| | r_{\pi}} v_{\text {in }} \\
v_{\text {out }}=-g_{\mathrm{m}} v_{\mathrm{be}}\left(r_{\mathrm{o}}| | R_{\mathrm{C}} \| \mid R_{3}\right)=-g_{\mathrm{m}}\left(r_{\mathrm{o}}| | R_{\mathrm{C}}| | R_{3}\right) \frac{R_{2}\left\|R_{4}\right\| r_{\pi}}{R_{\mathrm{I}}+R_{2}| | R_{4}| | r_{\pi}} v_{\text {in }} \\
A_{\mathrm{v}}=\frac{v_{\text {out }}}{v_{\mathrm{in}}}=-g_{\mathrm{m}}\left(r_{\mathrm{o}}| | R_{\mathrm{C}}| | R_{3}\right) \frac{R_{2}| | R_{4}| | r_{\pi}}{R_{\mathrm{I}}+R_{2}| | R_{4}| | r_{\pi}} \\
=-(12.4 \mathrm{mS})(12.92 \mathrm{k} \Omega)\left(\frac{9.46 \mathrm{k} \Omega}{1 \mathrm{k} \Omega+9.46 \mathrm{k} \Omega}\right) \\
A_{\mathrm{V}}=-137.3 \mathrm{~V} / \mathrm{V}
\end{gathered}
$$

Note that the voltage gain is negative. This is because the current passing through $r_{0}$ is moving upwards, while $v_{o u t}$ is defined as the voltage drop across $r_{0}$ in the opposite direction. Physically, this means that the output signal is $180^{\circ}$ out of phase with the input signal.
c. Repeat part (b) with $\mathrm{R}_{\mathrm{E}}=80 \mathrm{k} \Omega$.

Following the exact same procedures as part (b), the following results are obtained:

$$
\begin{array}{|l|}
\hline I_{\mathrm{B}}=0.388 \mu \mathrm{~A} \\
\hline \hline I_{\mathrm{C}}=50.4 \mu \mathrm{~A} \\
\hline \hline I_{\mathrm{E}}=50.8 \mu \mathrm{~A} \\
\hline \\
\hline V_{\mathrm{B}}=4.76 \mathrm{~V} \\
\hline \hline V_{\mathrm{C}}=11.24 \mathrm{~V} \\
\hline \hline V_{\mathrm{E}}=4.06 \mathrm{~V} \\
\hline
\end{array}
$$

$g_{\mathrm{m}}=1.95 \mathrm{mS}$
$r_{\pi}=66.8 \mathrm{k} \Omega$
$r_{0}=1.33 \mathrm{M} \Omega$
$A_{\mathrm{v}}=-24.6 \mathrm{~V} / \mathrm{V}$
d. If the goal is to maximize the voltage gain, what general design rule for commonemitter amplifiers can you infer from the results of parts (b) and (c)?

In general, we want the emitter resistor to be as low as possible.
2) Purpose: Coupling diodes and BJTs.

In the circuit below, find the Q-point of both the Zener diode and BJT. Assume the BJT is biased in the forward-active regime, that $\mathrm{V}_{\mathrm{Z}}=5 \mathrm{~V}, \mathrm{R}_{\mathrm{Z}}=0 \Omega, \beta=100$, and $\mathrm{V}_{\mathrm{BE}}=0.7 \mathrm{~V}$.


Figure 2: Zener diode with BJT.


Figure 2S: Zener diode in breakdown regime, represented as a DC voltage source.

From inspection of the circuit, and if we are assuming the BJT is biased in the forward-active regime, it is safe to assume the Zener diode is operating in the breakdown regime. Therefore, we can replace it with a 5 V DC source, as seen in Figure 2S.

## Starting KVL from the power supply,

$$
\begin{gathered}
12 \mathrm{~V}-\left(I_{\mathrm{C}}+I_{\mathrm{B}}\right) R_{\mathrm{C}}-V_{\mathrm{Z}}-V_{\mathrm{BE}}-I_{\mathrm{E}} R_{\mathrm{E}}=\mathbf{0} \\
12 \mathrm{~V}-(\beta+1) I_{\mathrm{B}} R_{\mathrm{C}}-V_{\mathrm{Z}}-V_{\mathrm{BE}}-(\beta+1) I_{\mathrm{B}} R_{\mathrm{E}}=0 \\
I_{\mathrm{B}}=\frac{\mathbf{1 2} \mathrm{V}-V_{\mathrm{Z}}-V_{\mathrm{BE}}}{(\beta+1)\left(R_{\mathrm{C}}+R_{\mathrm{E}}\right)}=\frac{6.3 \mathrm{~V}}{(101)(\mathbf{3 5 0 0} \Omega)} \\
I_{\mathrm{B}}=17.8 \mu \mathrm{~A} \\
I_{\mathrm{C}}=\beta I_{\mathrm{B}}=1.78 \mathrm{~mA} \\
I_{\mathrm{E}}=(\beta+1) I_{\mathrm{B}}=1.80 \mathrm{~mA}
\end{gathered}
$$

$$
\begin{gathered}
V_{\mathrm{C}}=12 \mathrm{~V}-I_{\mathrm{E}} R_{\mathrm{C}}=12 \mathrm{~V}-(1.80 \mathrm{~mA})(500 \Omega) \\
V_{\mathrm{C}}=11.1 \mathrm{~V}
\end{gathered}
$$

$$
V_{\mathrm{B}}=V_{\mathrm{C}}-V_{\mathrm{Z}}=11.1 \mathrm{~V}-5 \mathrm{~V}
$$

$$
V_{\mathrm{B}}=6.1 \mathrm{~V}
$$

$$
V_{\mathrm{E}}=V_{\mathrm{B}}-V_{\mathrm{BE}}=6.1 \mathrm{~V}-0.7 \mathrm{~V}
$$

$$
V_{\mathrm{E}}=5.4 \mathrm{~V}
$$

Obviously, from inspection, the current through the Zener diode is the current that goes directly into the base of the BJT. Therefore,

$$
I_{\mathrm{Z}}=I_{\mathrm{B}}=17.8 \mu \mathrm{~A}
$$

And, of course, given from the problem statement, $V_{\mathrm{Z}}=5 \mathrm{~V}$
3. Purpose: BJT application in circuit designing

Assume forward active mode bias and identical BJTs $\mathrm{Q}_{1}$ and $\mathrm{Q}_{2}$ in the following "current mirror" circuit.
Given, $R_{2}=10 \mathrm{k} \Omega, R_{3}=1 \mathrm{k} \Omega, R_{7}=100 \Omega, R_{8}=100 \Omega, \beta=416.4$, and $\mathrm{I}_{\mathrm{S}}=6.73 \mathrm{fA}$.
(a) Find the current flowing in $R_{3}$ and compare it to the current flowing in $R_{2}$. Note: it may be helpful to use Ebers Moll model only for determining collector currents in the two transistors, but otherwise use Beta/CVD model.
(b) What happens to the currents if $R_{3}$ is replaced with a $5 \mathrm{k} \Omega$ resistor?


Figure 3. Current mirror circuit.
(a)
$V_{\mathrm{B}}$ is same for both $\mathrm{Q}_{1}$ and $\mathrm{Q}_{2}$ transistors, so is $V_{\mathrm{E}}$. Also, $V_{\mathrm{C} 1}=V_{\mathrm{B} 1}$.
Since, $V_{\mathrm{E} 1}=V_{\mathrm{E} 2}$ and $R_{8}=R_{7}$, we can calculate, $I_{\mathrm{E} 1}=I_{\mathrm{E} 2}$.
We know,

$$
\begin{gathered}
I_{\mathrm{E}}=\left(\frac{\beta+1}{\beta}\right) I_{\mathrm{C}} \\
I_{\mathrm{B}}=\frac{I_{\mathrm{C}}}{\beta}
\end{gathered}
$$

Now,

$$
\begin{gathered}
15 \mathrm{~V}=I_{\mathrm{E} 1} R_{8}+0.7+R_{2}\left(I_{C 1}+2 I_{B}\right) \\
\Rightarrow I_{C 1}=\frac{15-0.7}{R_{2}\left(\frac{2}{\beta}\right)+R_{2}+\left(\frac{\beta+1}{\beta}\right) R_{8}}=1.409 \mathrm{~mA}
\end{gathered}
$$

So,

$$
I_{E 1}=\left(\frac{\beta+1}{\beta}\right) I_{\mathrm{C} 1}=1.412 \mathrm{~mA}
$$

Since, $V_{B E 1}=V_{B E 2}$ and $I_{C}=I_{S} e^{V_{B E} / V_{T}}$,

$$
I_{C 1}=I_{C 2}=1.409 \mathrm{~mA}
$$

(b)

Nothing changes if $R_{3}=5 k \Omega$, since the current through collector ( $I_{C 2}$ ) is set by $Q_{1}$. The circuit acts as a dc current source as long as $Q_{1}$ and $Q_{2}$ remain forward active. For this to happen, Ic must not be too high. Ic are set by $R_{2}$ (primarily) and $R_{8}+R_{7}$. Also, for $I_{C 1}=I_{C 2}$, the choice of $R_{8}=R_{7}$ was important.

Note, multiple current sources can be made from this configuration. For this configuration, common power supply is not required, only common ground is necessary.


